

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Description

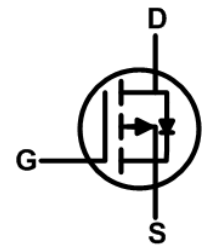
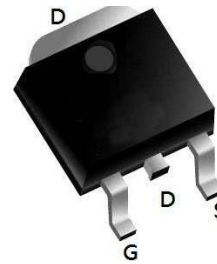
The XXW40P03 is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications .

The XXW40P03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Product Summary

BVDSS	R _{DS(on)}	I _D
-30V	18 mΩ	-40A

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V _{DS}	Drain-Source Voltage	-30		V
V _{GS}	Gate-Source Voltage	±20		V
I _{D@Tc=25°C}	Continuous Drain Current, V _{GS} @ -10V ¹	- 40		A
I _{D@Tc=100°C}	Continuous Drain Current, V _{GS} @ -10V ¹	-17		A
I _{DM}	Pulsed Drain Current ²	-80		A
EAS	Single Pulse Avalanche Energy ³	35		mJ
I _{AS}	Avalanche Current	-10		A
P _{D@TA=25°C}	Total Power Dissipation ⁴	4.0		W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	32	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D = -250\mu A$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V,$	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance Note3	$V_{GS} = -10V, I_D = -9A$	-	18	25	m Ω
		$V_{GS} = -4.5V, I_D = -5A$	-	27	38	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$	-	1200	-	pF
C_{oss}	Output Capacitance		-	155	-	pF
C_{rss}	Reverse Transfer Capacitance		-	139	-	pF
Q_g	Total Gate Charge	$V_{DS} = -15V, I_D = -8A,$ $V_{GS} = -10V$	-	52	-	nC
Q_{gs}	Gate-Source Charge		-	9.8	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	8.3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -15V, I_D = -1A,$ $V_{GS} = -10V, R_{GEN} = 6\Omega$	-	13	-	ns
t_r	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	198	-	ns
t_f	Turn-off Fall Time		-	98	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-35	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-80	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S = -9A$	-	-0.8	-1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=-15V$, $V_G=-10V$, $R_G=25\Omega$, $L=0.5mH$, $I_{AS}=-10A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

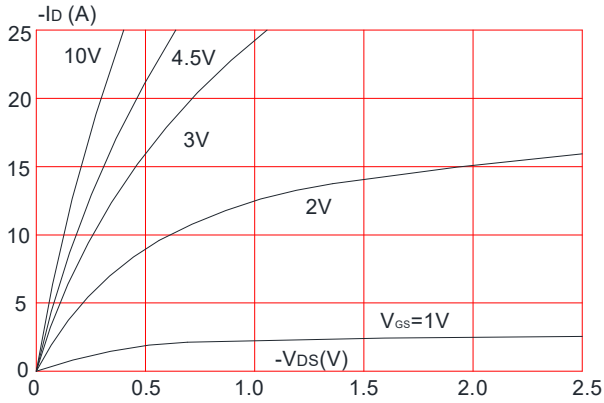
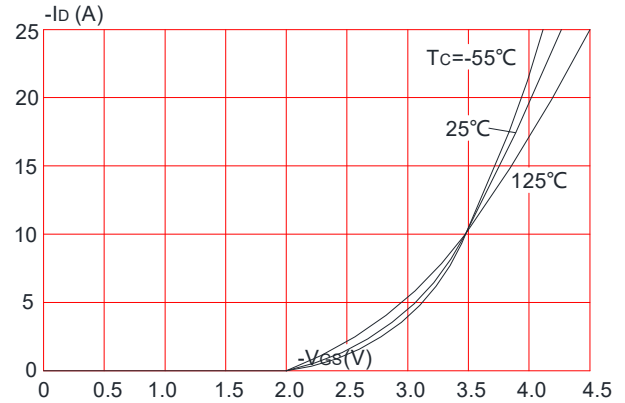
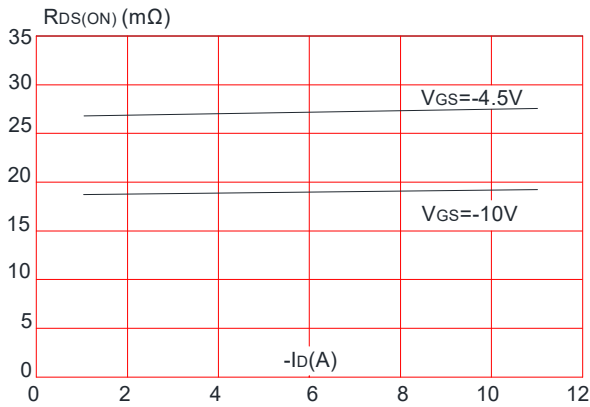
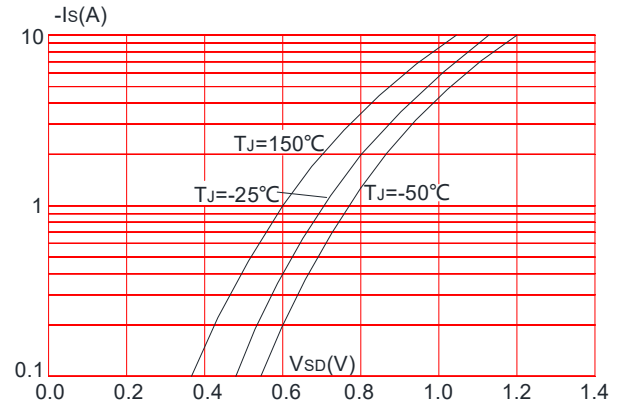
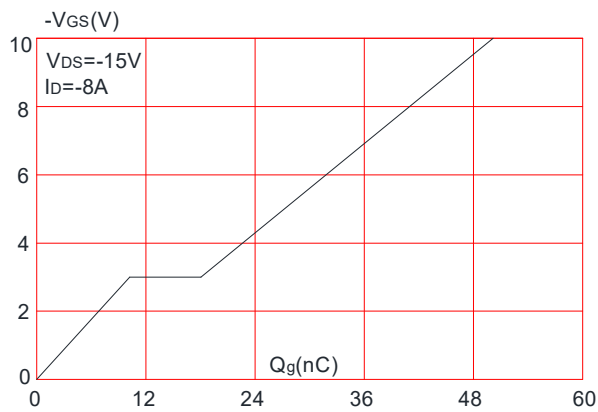
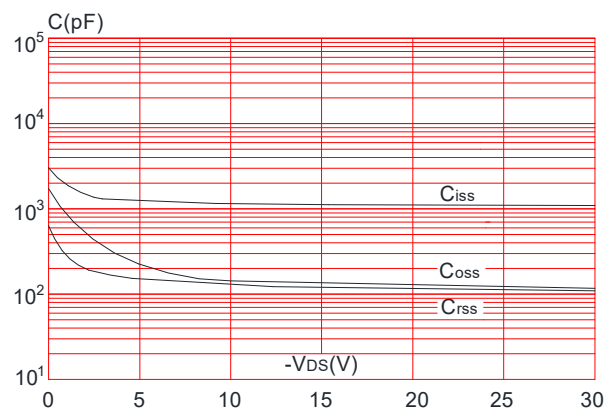
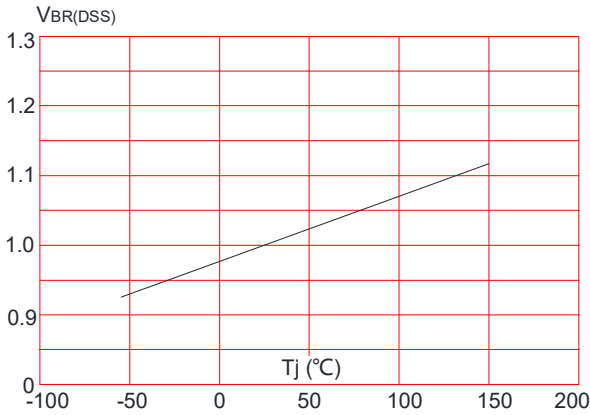
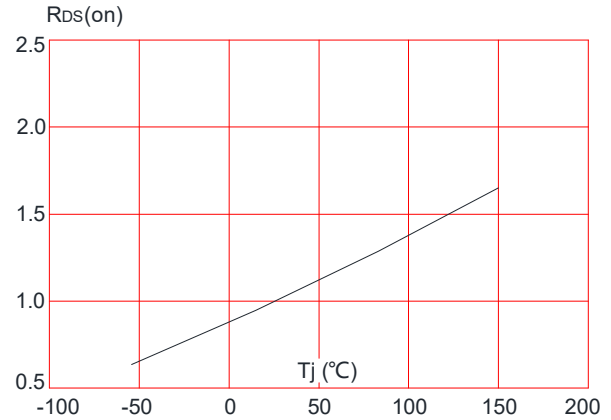
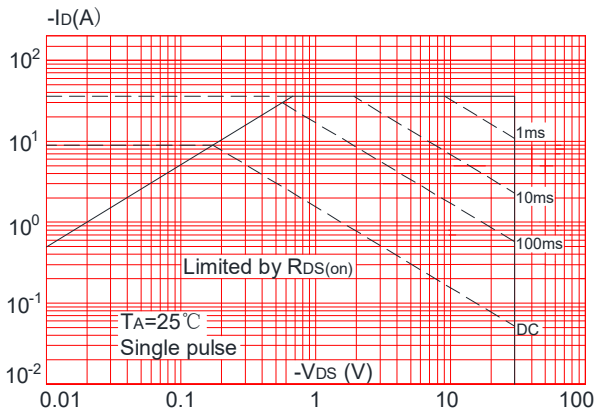
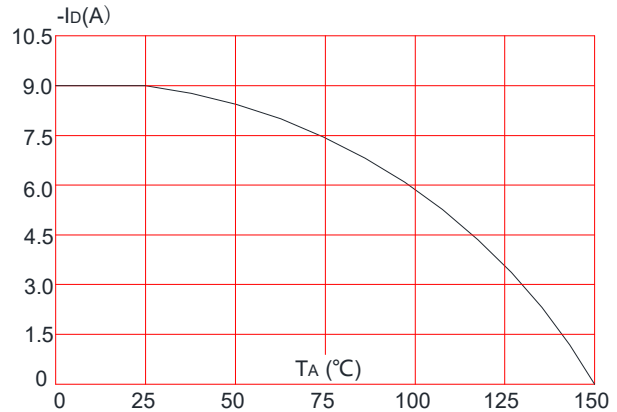
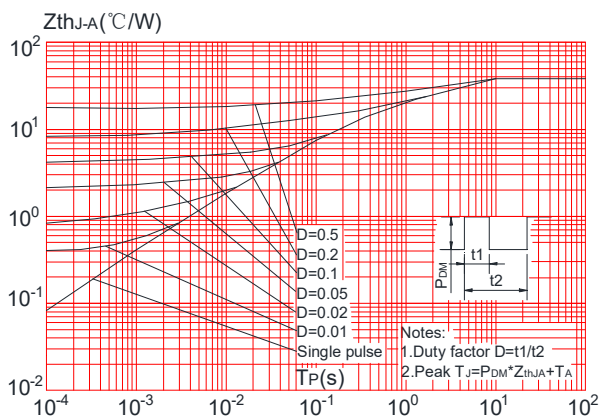
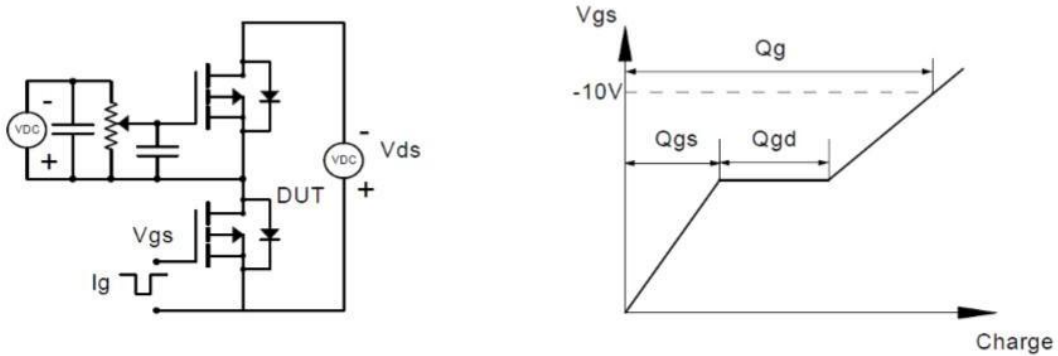
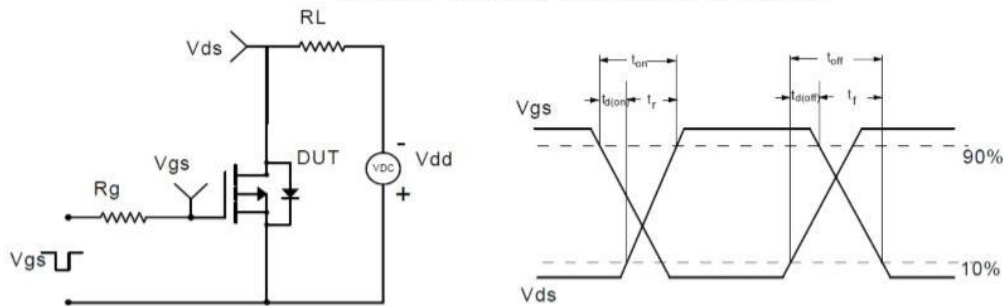
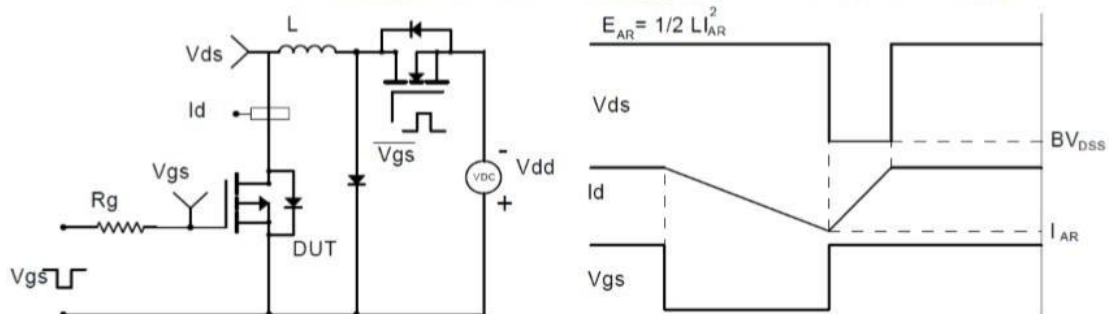
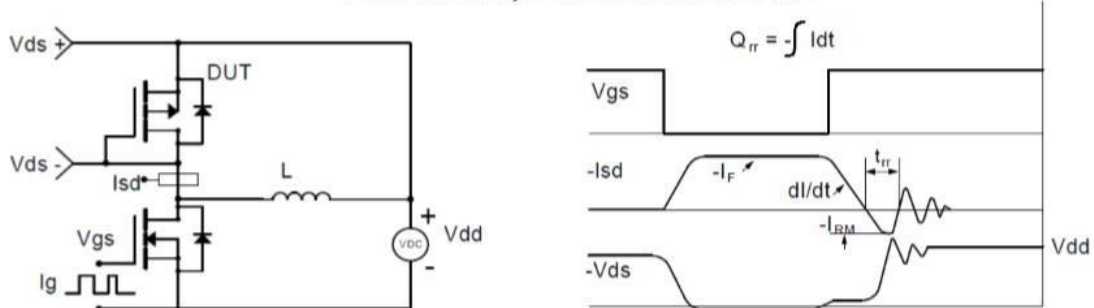
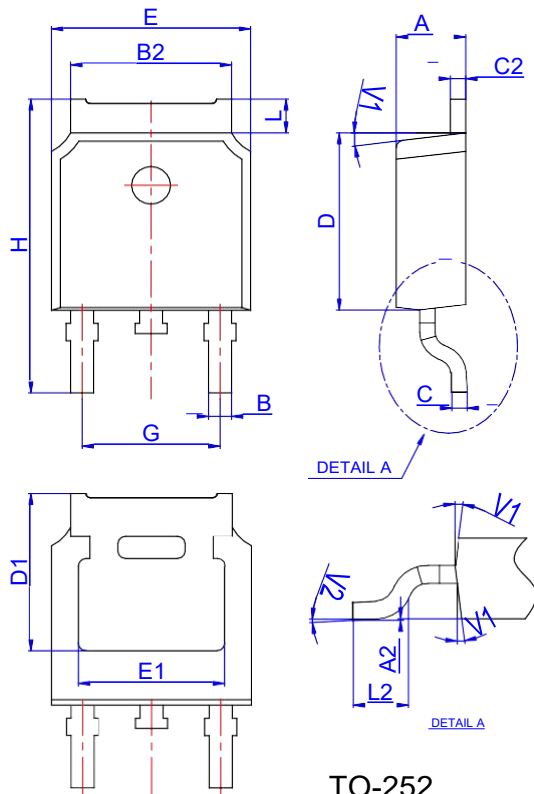
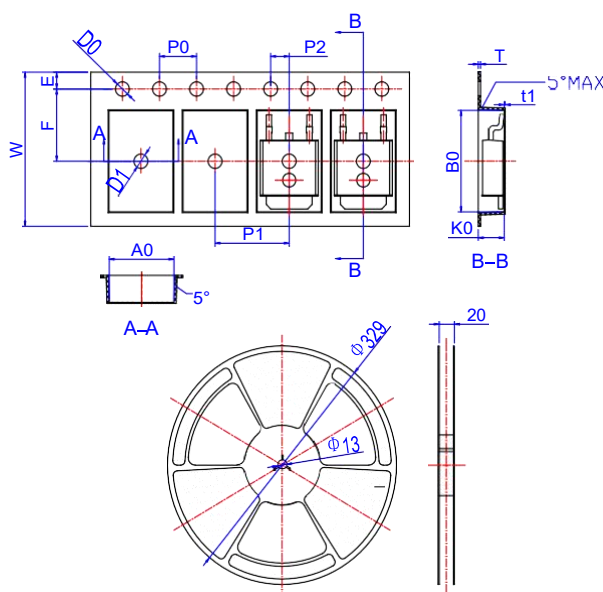
Figure 1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

Figure 8: Normalized on Resistance vs. Junction Temperature

Figure 9: Maximum Safe Operating Area

Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Test Circuit
Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

Diode Recovery Test Circuit & Waveforms


Package Mechanical Data TO 252


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°	0°		6°

Reel Specification-TO-252-4R


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583